TOSHIBA 1SS193

TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

1 S S 1 9 3

ULTRA HIGH SPEED SWITCHING APPLICATION.

Small Package : SC-59

: $V_{F(3)} = 0.9V$ (Typ.) Low Forward Voltage

Fast Reverse Recovery Time : $t_{rr} = 1.6$ ns (Typ.)

Small Total Capacitance $: C_T = 0.9pF (Typ.)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL RATING		UNIT
Maximum (Peak) Reverse Voltage	v_{RM}	85	V
Reverse Voltage	$v_{ m R}$	80	V 4
Maximum (Peak) Forward Current	$I_{ extbf{FM}}$	300	mA
Average Forward Current	IO	100	mA
Surge Current (10ms)	IFSM	2	A
Power Dissipation	P	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$ m T_{stg}$	-55~125	°C

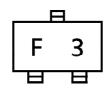
Unit in mm 1. ANODE 2. N.C. 3. CATHODE S-MINI **JEDEC** TO-236MOD EIAJ SC-59 TOSHIBA 1-3G1B

Weight: 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{F (1)}	I _F =1mA	_	0.60	_	v
	$V_{F(2)}$	$I_{ m F}$ = 10mA		0.72		
	$V_{F(3)}$	$I_{ m F}$ = 100mA	_	0.90	1.20	
Reverse Current $ \frac{I_{R(1)}}{I_{R(2)}} $	I _{R (1)}	$V_{R}=30V$	_	_	0.1	
	$V_R = 80V$	_	_	0.5	μ A	
Total Capacitance	$\mathbf{C_T}$	$V_R=0$, f=1MHz		0.9	3.0	рF
Reverse Recovery Time	t _{rr}	I _F =10mA (Fig.1)	_	1.6	4.0	ns

MARKING



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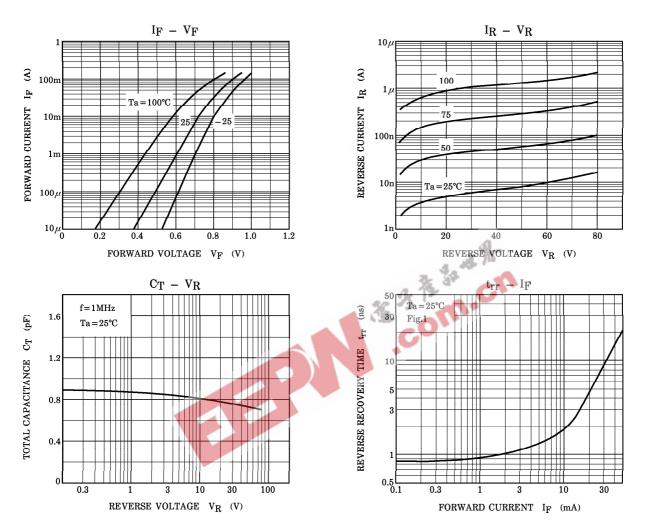
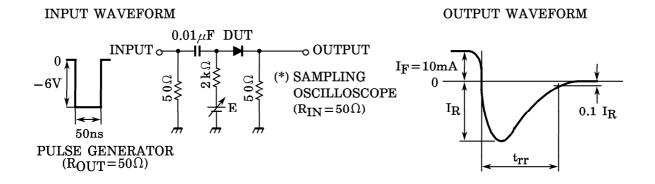


Fig.1 Reverse recovery time (t_{rr}) test circuit



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